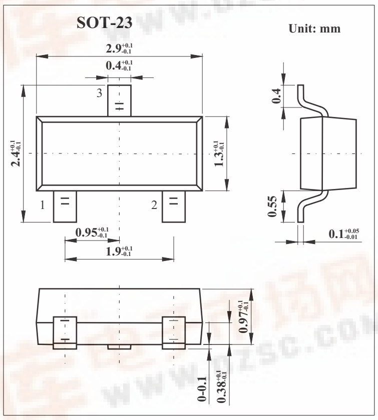
Silicon Schottky Barrier Diode

HRW0202B

Features

- Low forward voltage drop and suitable for high effifiency rectifying.
- MPAK package is suittable for high density surface mounting and high speed assembly.



Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	20	V
Average rectified current	I_O	200	mA
Non-repetitive peak forward surge current	I_{FSM}	3	A
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to + 125	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	I_F = 100 mA			0.42	V
Reverse current	I_R	V_R = 20 V			10	µA
Thermal resistance	$T_{sh(j-a)}$	Polyimide board		400		℃/W

Marking

Marking	S18